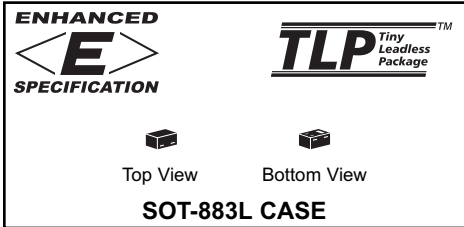




CET3904E NPN
CET3906E PNP

**ENHANCED SPECIFICATION
COMPLEMENTARY PICOmini™
SILICON TRANSISTORS**



Central™

Semiconductor Corp.

DESCRIPTION:

The Central Semiconductor CET3904E / CET3906E Low $V_{CE(SAT)}$ NPN and PNP Transistors, respectively, are designed for applications where ultra small size and power dissipation are the prime requirements. Packaged in a Tiny Leadless Package TLP™, these components provide performance characteristics suitable for the most demanding size constrained applications.

MARKING CODES: CET3904E: C
CET3906E: D

FEATURES:

- Device is **Halogen Free** by design
- Power Dissipation 250mW
- Low $V_{CE(SAT)}$ 0.1V Typ @ 50mA
- Small, TLP™ 1x0.4mm, SOT-883L Leadless, Low Profile, Surface Mount Package

APPLICATIONS:

- DC / DC Converters
- Battery powered devices including Cell Phones and Digital Cameras

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

◆ Collector-Base Voltage	
Collector-Emitter Voltage	
◆ Emitter-Base Voltage	
Collector Current	
Power Dissipation (Note 1)	
Power Dissipation (Note 2)	
Operating and Storage Junction Temperature	
Thermal Resistance (Note 1)	
Thermal Resistance (Note 2)	

SYMBOL		UNITS
V_{CBO}	60	V
V_{CEO}	40	V
V_{EBO}	6.0	V
I_C	200	mA
P_D	250	mW
P_D	430	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Θ_{JA}	500	$^\circ\text{C/W}$
Θ_{JA}	290	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	<u>NPN</u>	<u>PNP</u>	MAX	UNITS
			TYP	TYP		
I_{CEV}	$V_{CE}=30V, V_{EB}=3.0V$				50	nA
◆ BV_{CBO}	$I_C=10\mu A$	60	115	90		V
BV_{CEO}	$I_C=1.0mA$	40	60	55		V
◆ BV_{EBO}	$I_E=10\mu A$	6.0	7.5	7.9		V
◆ $V_{CE(SAT)}$	$I_C=10mA, I_B=1.0mA$		0.057	0.050	0.100	V
◆ Enhanced specification						

Notes: (1) FR-4 epoxy PC board, standard mounting conditions
(2) FR-4 epoxy PC board with collector mounting pad area of 1 cm²

R1 (5-MAY 2008)

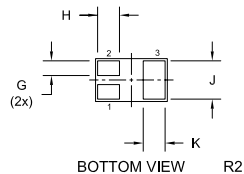
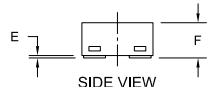
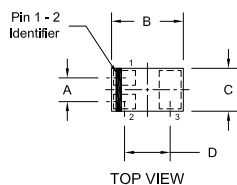
ENHANCED SPECIFICATION COMPLEMENTARY PICOMiniTM SILICON TRANSISTORS

ELECTRICAL CHARACTERISTICS - Continued:

SYMBOL	TEST CONDITIONS	MIN	NPN TYP	PNP TYP	MAX	UNITS
◆ $V_{CE(SAT)}$	$I_C=50mA, I_B=5.0mA$		0.100	0.100	0.200	V
$V_{BE(SAT)}$	$I_C=10mA, I_B=1.0mA$	0.65	0.75	0.75	0.85	V
$V_{BE(SAT)}$	$I_C=50mA, I_B=5.0mA$		0.85	0.85	0.95	V
◆ h_{FE}	$V_{CE}=1.0V, I_C=0.1mA$	90	240	130		
◆ h_{FE}	$V_{CE}=1.0V, I_C=1.0mA$	100	235	150		
h_{FE}	$V_{CE}=1.0V, I_C=10mA$	100	215	150	300	
◆ h_{FE}	$V_{CE}=1.0V, I_C=50mA$	70	110	120		
h_{FE}	$V_{CE}=1.0V, I_C=100mA$	30	50	55		
f_T	$V_{CE}=20V, I_C=10mA, f=100MHz$	300				MHz
C_{ob}	$V_{CB}=5.0V, I_E=0, f=1.0MHz$				4.0	pF
C_{ib}	$V_{BE}=0.5V, I_C=0, f=1.0MHz$				8.0	pF
h_{ie}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	1.0			12	k Ω
h_{re}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	0.1			10	$\times 10^{-4}$
h_{fe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	100			400	
h_{oe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	1.0			60	μS
NF	$V_{CE}=5.0V, I_C=100\mu A, R_S=1.0K\Omega, f=10Hz$ to 15.7kHz				4.0	dB
t_d	$V_{CC}=3.0V, V_{BE}=0.5V, I_C=10mA, I_{B1}=1.0mA$				35	ns
t_r	$V_{CC}=3.0V, V_{BE}=0.5V, I_C=10mA, I_{B1}=1.0mA$				35	ns
t_s	$V_{CC}=3.0V, I_C=10mA, I_{B1}=I_{B2}=1.0mA$				200	ns
t_f	$V_{CC}=3.0V, I_C=10mA, I_{B1}=I_{B2}=1.0mA$				50	ns

◆ Enhanced specification

SOT-883L - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.014		0.35	
B	0.037	0.041	0.95	1.05
C	0.022	0.026	0.55	0.65
D	0.026		0.65	
E	0.000	0.002	0.00	0.05
F	0.012	0.016	0.30	0.40
G	0.005	0.007	0.13	0.18
H	0.008	0.012	0.20	0.30
J	0.018	0.022	0.45	0.55
K	0.008	0.012	0.20	0.30

SOT-883L (REV:R2)

LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

R1 (5-MAY 2008)